EXPRESS MAIL LABEL NO. EV296621110US

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.:

Unknown

Filed:

Title:

March 10, 2004

Group Art Unit:

Unknown

Examiner:

Unknown

Applicant:

Pradip K. Roy, Anthony Dip, Allen J. Leith, Seungho Oh SILICON-GERMANIUM THIN LAYER SEMICONDUCTOR

STRUCTURE WITH VARIABLE SILICON-GERMANIUM

COMPOSITION AND METHOD OF FABRICATION

Attorney Docket:

TPS-008

Cincinnati, Ohio 45202

March 10, 2004

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

INFORMATION DISCLOSURE STATEMENT

In accordance with the duty of candor and good faith imposed by 37 C.F.R. §1.56 and means of complying therewith according to 37 C.F.R. §\$1.97 and 1.98, the references listed on the attached Form PTO-1449 are called to the attention of the United States Patent and Trademark Office in connection with the above-identified patent application.

Because the requirement (37 C.F.R. §1.98(a)(2)(i)) for submitting copies of U.S. patents and published applications has been waived, copies of only the foreign cited references and other documents are enclosed herewith.

No representation is made that the cited art is the only art or that the cited art represents the best art.

The Examiner is urged to consider all of the cited documents and to make an independent evaluation of the teachings and materiality of each.

If any additional fees are necessary to complete this communication, please apply them to Deposit Account No. 23-3000.

Respectfully submitted,

WOOD, HERRON & EVANS, L.L.P.

By:_

Kristi L. Davidson, Reg. No. 44,643

2700 Carew Tower
441 Vine Street
Cincinnati, OH 45202
(513) 241-2324 (voice)
(513) 241-6234 (facsimile)
K:\TPS\008\UDS.wpd

Sheet	1 1 (<u>(A)</u>	_ of	1

SUBSTITUTE (MODIFIED)	SUBSTITUTE FORM PTO-1449 (MODIFIED)						U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. TPS/008			SERIAL NO. Unknown		
	INFORMATION DISCLOSURE STATEMENT BY APPLICANT										APPLICANT Pradip K. Roy et al.				
(37 CFR 1.98	(Use several sheets if necessary) 98(b))							ecessary)			FILING DATE March 10, 2004			GROUP Unknown	
								U.S. F	PATENT D	OCUMENTS					
EXAMINER INITIAL		PATENT NUMBER						ISSUE DATE PATENTEE			CLASS		SUBCLASS		FILING DATE IF APPROPRIATE
	A.A														
	A.B														
	A.C		Ш												
	A.D												ļ		
	A.E	_		_		$\downarrow \downarrow$						-	ļ	-	
	A.F	_			_	\sqcup						ļ			
	A.G			_								ļ		· · · · · · ·	
	A.H			\perp	_	\sqcup						ļ	<u> </u>		ļ
	A.I		\square	\dashv	+	\sqcup						<u> </u>	<u> </u>		
· · · · · · · · · · · · · · · · · · ·	A.J	\bot			+	\perp						ļ			
	A.K											1	<u> </u>		
	ı .					IGN I				FOREIGN PA		APPLICATIO	NS I	т	
		DOCUMENT NUMBER				PUBLICATION DATE			COUNTRY OR PATENT OFFICE		CLASS	SUBCL	ASS	TRANSLATION (YES/NO)	
	A.L	EP0684650 B1				08/29/2001 EF				ı	H01L	29/786			
	A.M								No.	98 20 E					
	A.N														
	A.O														
	A.P														
	A.Q														
	_				ОТН	ER D	OCL	JMENTS (Incli	uding Auth	or, Title, Date	, Place	of Publicatio	n)		
	A.R	Ste Edi	pher tion,	n St. pp 1	Onge 95-19	and 1	Mark blish	Dupuis, <u>Inno</u> led July, 2000	vations in .	Silicon Germa	anium B	icmos Proce	ssing, Sen	niconduc	ctor Fabtech - 12th
	A.S														
	A.T														
EXAMINER										DATE CONS	IDEREC)			
EXAMINER: I	nitial if ci	itation	con	ıside	red, v	vhethe	er or	not in conform	nance. Dr	raw line throug	h citatio	on only if not	in conform	nance an	nd not considered.

EXAMINER: Initial if citation considered, whether or not in conformance. Draw line through citation only if not in conformance and not considered Include a copy of this form with next communication to Applicant.